

Anup P Omprakash

List of Publications by Year in descending order

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223
citing authors

#	ARTICLE	IF	CITATIONS
1	Comparison of Single-Event Transients in SiGe HBTs on Bulk and Thick-Film SOI. IEEE Transactions on Nuclear Science, 2020, 67, 71-80.	2.0	7
2	Single-Event Transients in SiGe HBTs Induced by Pulsed X-Ray Microbeam. IEEE Transactions on Nuclear Science, 2020, 67, 91-98.	2.0	4
3	Investigation of f_T -Doubler Technique to Improve RF Performance of Inverse-Mode SiGe HBTs. IEEE Microwave and Wireless Components Letters, 2020, 30, 873-875.	3.2	5
4	DC and RF Variability of SiGe HBTs Operating Down to Deep Cryogenic Temperatures. , 2019, , .		6
5	The Effects of Temperature on the Single-Event Transient Response of a High-Voltage (>30 V) Complementary SiGe-on-SOI Technology. IEEE Transactions on Nuclear Science, 2019, 66, 389-396.	2.0	1
6	Hot-Carrier-Damage-Induced Current Gain Enhancement (CGE) Effects in SiGe HBTs. IEEE Transactions on Electron Devices, 2018, 65, 2430-2438.	3.0	11
7	Using SiGe-on-SOI HBTs to Build 300°C Capable Analog Circuits. , 2018, , .		1
8	Collector Transport in SiGe HBTs Operating at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2018, 65, 3697-3703.	3.0	15
9	Operation of SiGe HBTs Down to 70 mK. IEEE Electron Device Letters, 2017, 38, 12-15.	3.9	28
10	Physical Differences in Hot Carrier Degradation of Oxide Interfaces in Complementary (n-p-n+p-n-p) SiGe HBTs. IEEE Transactions on Electron Devices, 2017, 64, 37-44.	3.0	10
11	An Investigation of High-Temperature (to 300°C) Safe-Operating-Area in a High-Voltage Complementary SiGe on SOI Technology. IEEE Transactions on Electron Devices, 2017, 64, 3748-3755.	3.0	5
12	Total Ionizing Dose Effects on a High-Voltage ($>30\text{V}$) Complementary SiGe on SOI Technology. IEEE Transactions on Nuclear Science, 2017, 64, 277-284.	2.0	5
13	On the Cryogenic RF Linearity of SiGe HBTs in a Fourth-Generation 90-nm SiGe BiCMOS Technology. IEEE Transactions on Electron Devices, 2015, 62, 1127-1135.	3.0	5
14	Single-Event Transient and Total Dose Response of Precision Voltage Reference Circuits Designed in a 90-nm SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2014, 61, 3210-3217.	2.0	22
15	On the cryogenic performance of ultra-low-loss, wideband SPDT RF switches designed in a 180 nm SOI-CMOS technology. , 2014, , .		1
16	A 0.8 THz f_{MAX} SiGe HBT Operating at 4.3 K. IEEE Electron Device Letters, 2014, 35, 151-153.	3.9	60